MC100EPT24

3.3V LVTTL/LVCMOS to Differential LVECL Translator

The MC100EPT24 is a LVTTL/LVCMOS to differential LVECL translator. Because LVECL levels and LVTTL/LVCMOS levels are used, a −3.3 V, +3.3 V and ground are required. The small outline 8−lead package and the single gate of the EPT24 makes it ideal for those applications where space, performance, and low power are at a premium.

- 350 ps Typical Propagation Delay
- Maximum Frequency > 1.0 GHz Typical
- The 100 Series Contains Temperature Compensation
- Operating Range: V_{CC} = 3.0 V to 3.6 V; V_{EE} = −3.6 V to −3.0 V; GND = 0 V
- PNP LVTTL Inputs for Minimal Loading
- Q Output Will Default HIGH with Input Open

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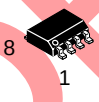
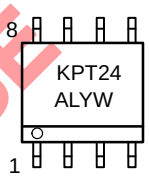
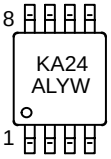
MARKING DIAGRAMS*



SO−8
D SUFFIX
CASE 751



TSSOP−8
DT SUFFIX
CASE 948R



A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week

*For additional information, see Application Note AND8002/D

ORDERING INFORMATION

Device	Package	Shipping
MC100EPT24D	SO−8	98 Units / Rail
MC100EPT24DR2	SO−8	2500 Tape & Reel
MC100EPT24DT	TSSOP−8	100 Units / Rail
MC100EPT24DTR2	TSSOP−8	2500 Tape & Reel

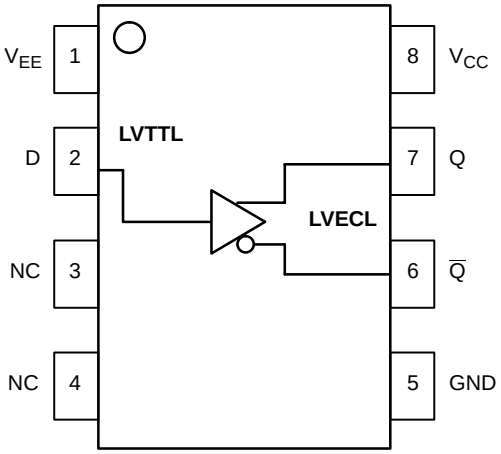


Figure 1. 8−Lead Pinout (Top View) **and Logic Diagram**

PIN DESCRIPTION

PIN	FUNCTION
Q, $\overline{Q}$	Differential LVECL Outputs
D	LVTTL Input
V_{CC}	Positive Supply
GND	Ground
V_{EE}	Negative Supply
NC	No Connect

ATTRIBUTES

Characteristics		Value
Internal Input Pulldown Resistor		N/A
Internal Input Pullup Resistor		N/A
ESD Protection	Human Body Model Machine Model Charged Device Model	> 4 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)		Level 1
Flammability Rating Oxygen Index		UL−94 code V−0 A 1/8” 28 to 34
Transistor Count		181 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test		

1. For additional information, see Application Note AND8003/D.

MAXIMUM RATINGS (Note 2)

Symbol	Parameter	Condition 1	Condition 2	Rating	Units
V_{CC}	Positive Power Supply	GND = 0 V	V_{EE} = −3.3 V	3.8	V
V_{EE}	Negative Power Supply	GND = 0 V	V_{CC} = +3.3 V	−3.8	V
V_{IN}	Input Voltage	GND = 0 V	$V_I \leq V_{CC}$	0 to V_{CC}	V
I_{out}	Output Current	Continuous Surge		50 100	mA mA
TA	Operating Temperature Range			−40 to +85	°C
T_{stg}	Storage Temperature Range			−65 to +150	°C
θ_{JA}	Thermal Resistance (Junction to Ambient)	0 LFPM 500 LFPM	8 SOIC 8 SOIC	190 130	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction to Case)	std bd	8 SOIC	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction to Ambient)	0 LFPM 500 LFPM	8 TSSOP 8 TSSOP	185 140	°C/W °C/W
θ_{JC}	Thermal Resistance (Junction to Case)	std bd	8 TSSOP	41 to 44	°C/W
T_{sol}	Wave Solder	<2 to 3 sec @ 248°C		265	°C

2. Maximum Ratings are those values beyond which device damage may occur.

LVTTL INPUT DC CHARACTERISTICS V_{CC}= 3.3 V, V_{EE}= −3.6 V to −3.0 V, GND= 0.0 V; T_A= −40°C to 85°C

Symbol	Characteristic	Condition	Min	Typ	Max	Unit
I_{IH}	Input HIGH Current	V_{IN} = 2.7 V			20	μA
I_{IHH}	Input HIGH Current	V_{IN} = 6.0 V			100	μA
I_{IL}	Input LOW Current	V_{IN} = 0.5 V			−0.6	mA
V_{IK}	Input Clamp Diode Voltage	I_{IN} = −18 mA			−1.2	V
V_{IH}	Input HIGH Voltage		2.0			V
V_{IL}	Input LOW Voltage				0.8	V

NECL OUTPUT DC CHARACTERISTICS V_{CC}= 3.3 V, V_{EE}= −3.3 V, GND= 0.0 V (Note 3)

		−40°C			25°C			85°C			
Symbol	Characteristic	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Unit
V_{OH}	Output HIGH Voltage (Note 4)	-1145	−1020	-895	-1145	−1020	-895	-1145	−1030	-895	mV
V_{OL}	Output LOW Voltage (Note 4)	-1945	−1820	-1695	-1945	−1820	-1695	-1945	−1820	-1695	mV
I_{CC}	Power Supply Current		2.0	4.0		2.0	4.0	2.0		4.0	mA
I_{EE}	Power Supply Current	20	30	38	20	30	38	20	30	38	mA

NOTE: Devices are designed to meet the DC specifications shown in the above table, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow greater than 500 lfpm is maintained.

3. Output levels will vary 1:1 with GND. V_{EE} can vary ± 0.3 V.
4. Outputs are terminated through a 50 ohm resistor to GND−2 volts.

AC CHARACTERISTICS V_{CC}= 3.0 V to 3.6 V, V_{EE}= −3.6 V to −3.0 V, GND= 0.0 V (Note 5)

		−40°C			25°C			85°C			
Symbol	Characteristic	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Unit
f_{max}	Maximum Frequency (See Figure 2. F_{max}/JITTER)		> 1			> 1			> 1		GHz
t_{PLH}, t_{PHL}	Propagation Delay to Output Differential (Note 6)	300	500	800	300	530	800	300	560	800	ps
t_{JITTER}	Cycle−to−Cycle Jitter (See Figure 2. F_{max}/JITTER)		0.2	< 1		0.2	< 1		0.2	< 1	ps
t_r t_f	Output Rise/Fall Times Q, $\overline{Q}$ (20% − 80%)	70	125	170	80	130	180	100	150	200	ps

5. Measured using a 750 mV source, 50% duty cycle clock source. All loading with 50 ohms to GND−2.0 V.
6. Specifications for standard TTL input signal.

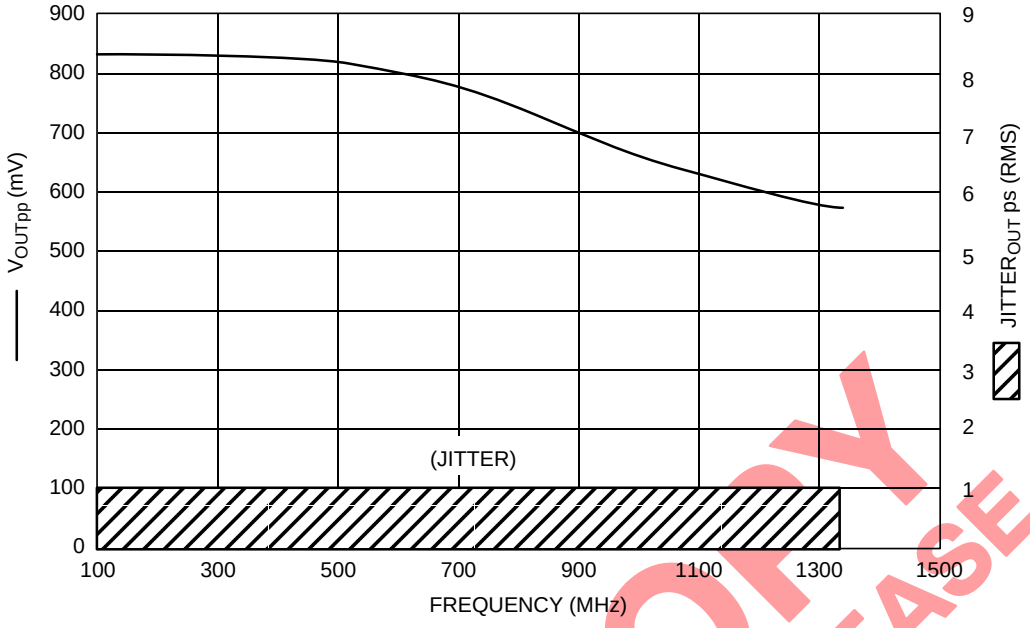


Figure 2. F_{max}/Jitter

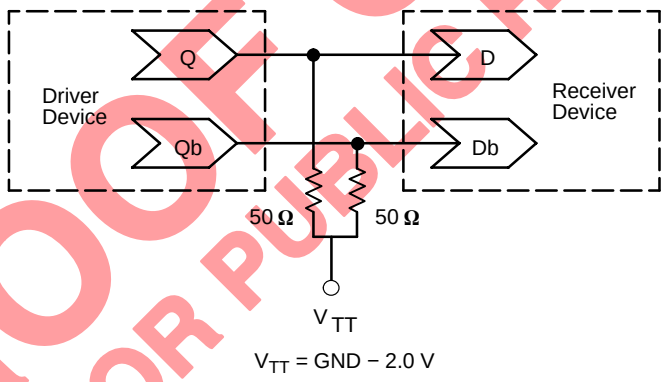


Figure 3. Typical Termination for Output Driver and Device Evaluation (See Application Note AND8020 − Termination of ECL Logic Devices.)

Resource Reference of Application Notes

AN1404 − ECLinPS Circuit Performance at Non−Standard V_{IH} Levels

AN1405 − ECL Clock Distribution Techniques

AN1406 − Designing with PECL (ECL at +5.0 V)

AN1504 − Metastability and the ECLinPS Family

AN1568 − Interfacing Between LVDS and ECL

AN1650 − Using Wire−OR Ties in ECLinPS Designs

AN1672 − The ECL Translator Guide

AND8001 − Odd Number Counters Design

AND8002 − Marking and Date Codes

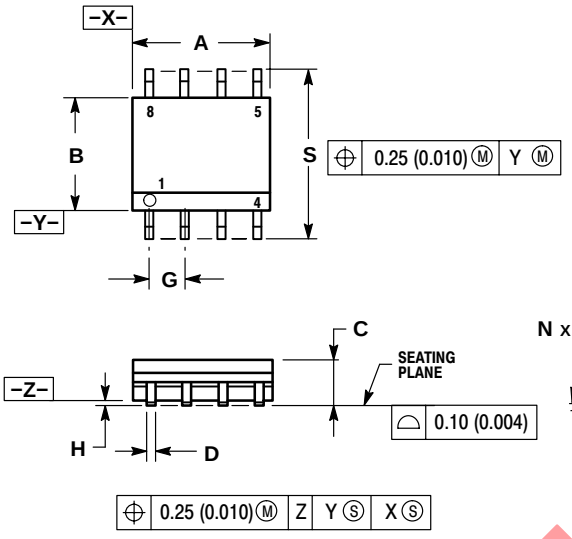
AND8009 − ECLinPS Plus Spice I/O Model Kit

AND8020 − Termination of ECL Logic Devices

For an updated list of Application Notes, please see our website at http://onsemi.com.

PACKAGE DIMENSIONS

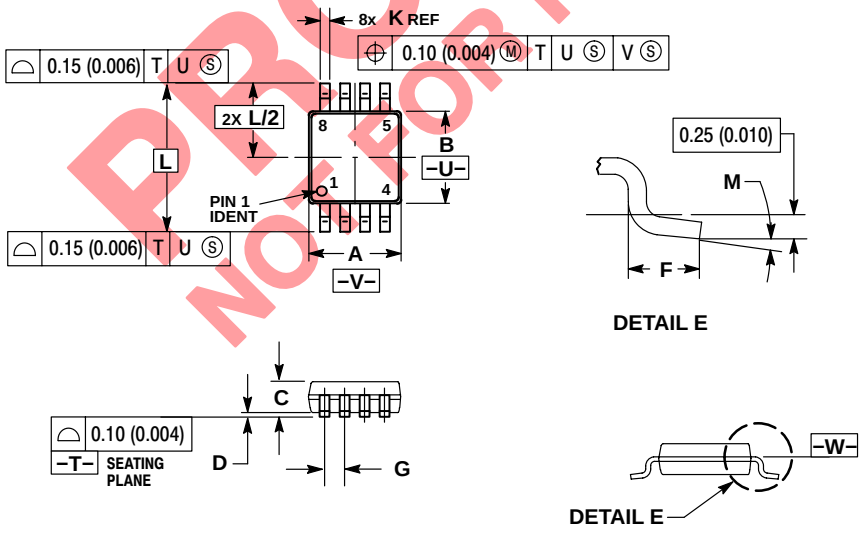
SO−8
D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751−07
ISSUE AA



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PEI SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

TSSOP−8
DT SUFFIX
PLASTIC TSSOP PACKAGE
CASE 948R−02
ISSUE A



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
M	0 °	6 °	0 °	6 °

Notes

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